

Percolation Threshold Effects on the Electrical Contact Resistance and Adhesion of Microelectromechanical Systems Thin-Film Materials

Daniel J. Dickrell III

Michael T. Dugger

James A. Knapp

David M. Follstaedt

Sandia National Laboratories

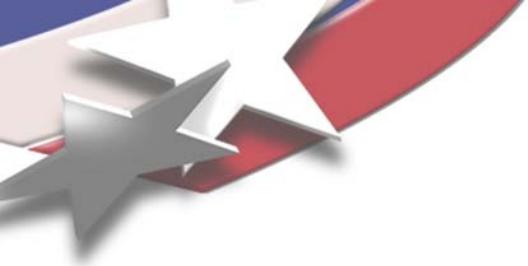
Material Science and Technology
Conference and Exhibition 2006

Philadelphia, PA

October 17th, 2006



Sandia National Laboratories

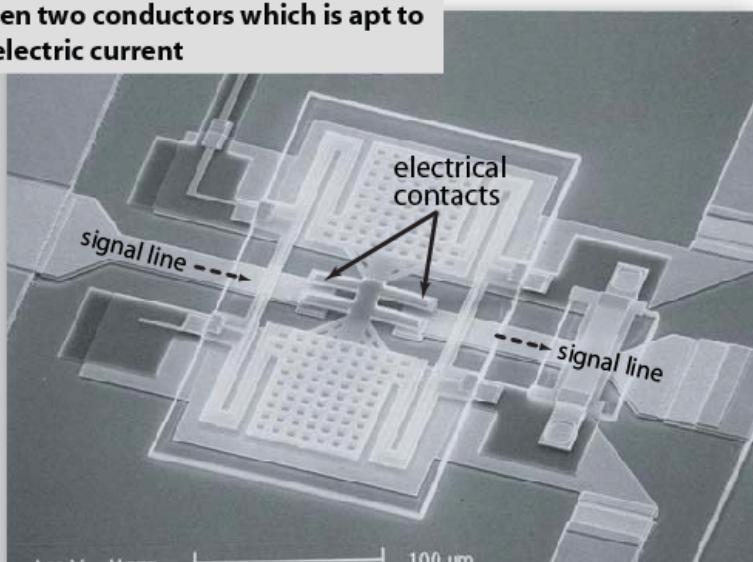


Presentation Outline

- **MEMS Electrical Contacts**
- **Degradation Mechanisms**
- **Composite Electrical Contact Materials**
- **Experimental Results**
- **Percolation Threshold**

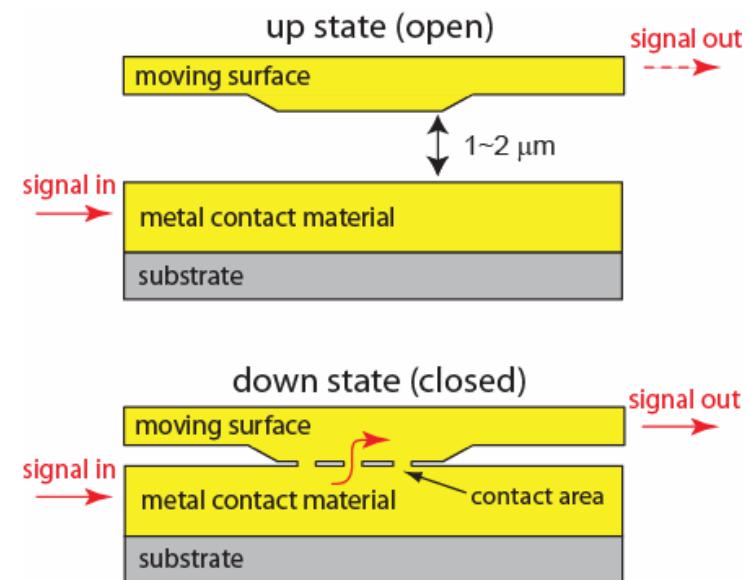
MEMS Electrical Contacts

electrical contact : a reasonable junction between two conductors which is apt to carry electric current



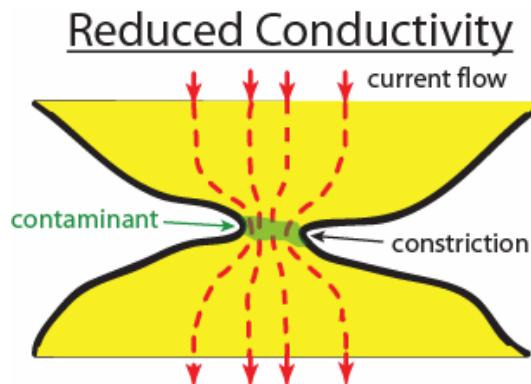
Rockwell RSC MEMS switch

Metal-contact MEMS electrical devices are capable of operating over a wide range of signal frequencies and posses distinct advantages over larger solid-state components: (e.g., size, low insertion loss, high isolation, low power consumption)



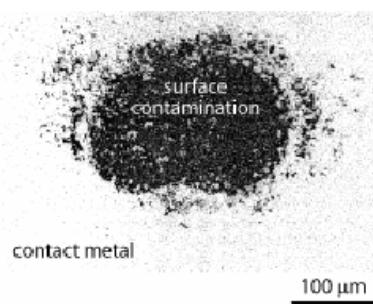
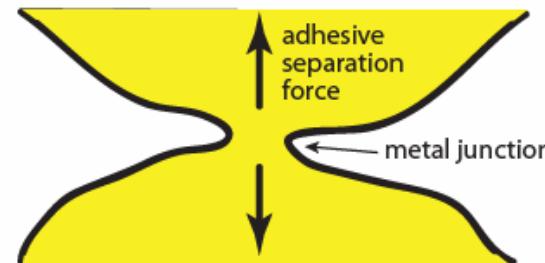
However, the performance and reliability of metal-contact MEMS devices depends critically on the *quality* of the electrical contact interfaces which can change over time

Degradation Mechanisms

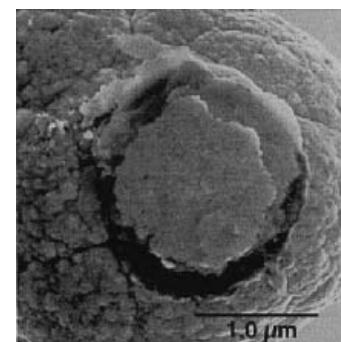


exclusive modes

Excess Adhesion



Tamal, T., 1995, "Effect of Silicone Vapour and Humidity on Contact Reliability of Micro Relay Contacts," *IEEE Transactions on Components, Packaging, and Manufacturing Technology – Part A*, 19(3), pp. 329-338.

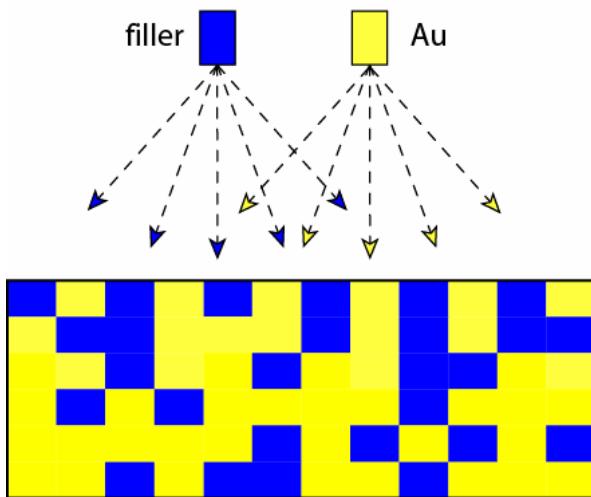


Hyman, D., and Mehregany, M., 1999, "Contact Physics of Gold Microcontacts for MEMS Switches," *IEEE Transactions on Components and Packaging Technology*, 22(3), pp. 357-364.

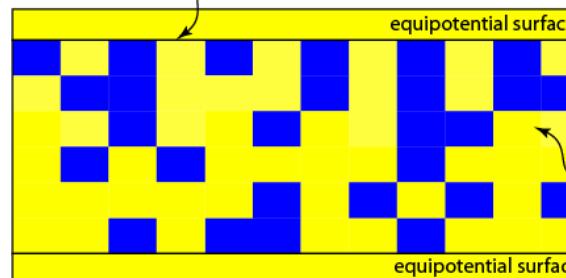
Proper operation of MEMS electrical contacts is predicated on the balance of sufficient interfacial conductivity and off-state separability of the surfaces

Composite Electrical Contact Materials

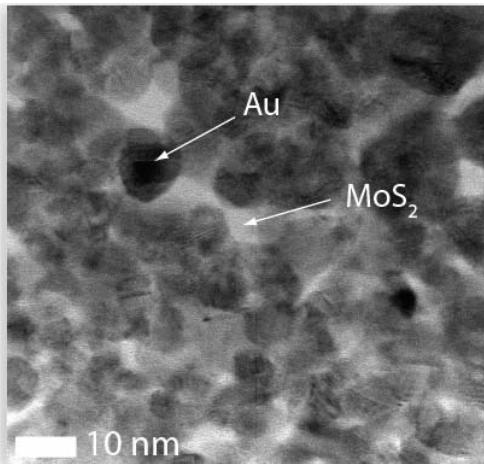
thin-film deposition



adhesion determined at interface



composite thin-film electrical contact



- J.R. Lince, "Tribology of co-sputtered nanocomposite Au/MoS₂ solid lubricant films over a wide contact stress range", *Tribology Letters*, Vol. 17, No. 3, 2004

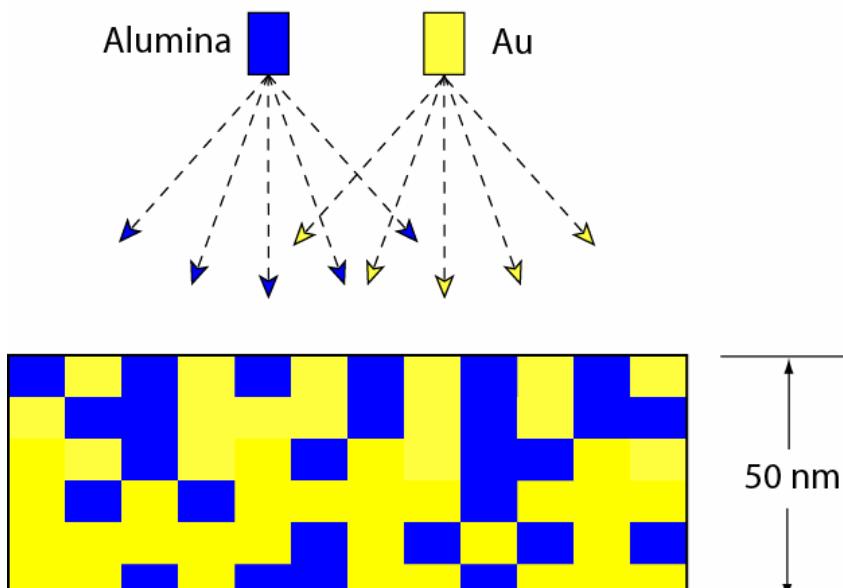
A co-deposited electrical contact material with intermixed phases of high-conductivity and low-adhesion constituents should satisfy the concurrent operational requirements of low resistance and reduced adhesion



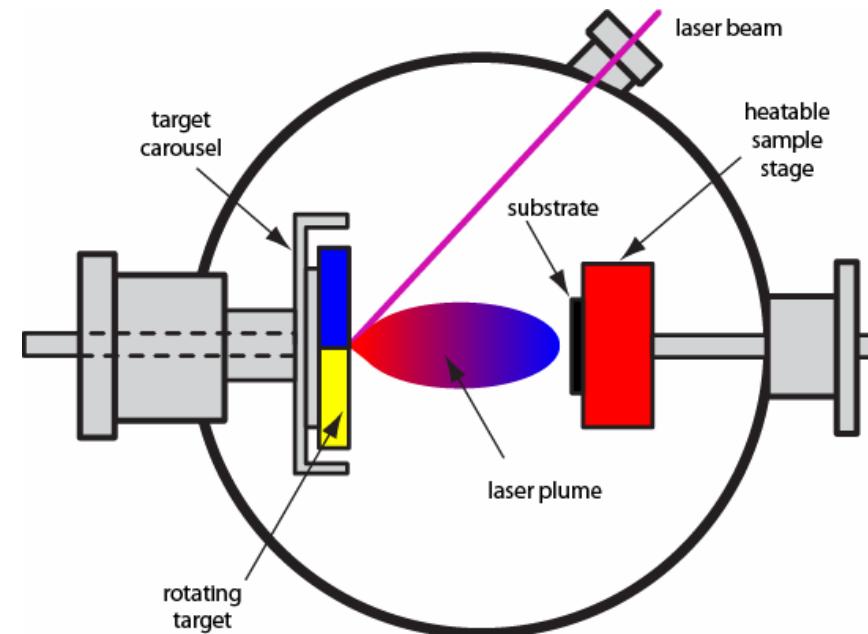
Sandia National Laboratories

Composite Material Deposition

Pulsed-Laser Deposition



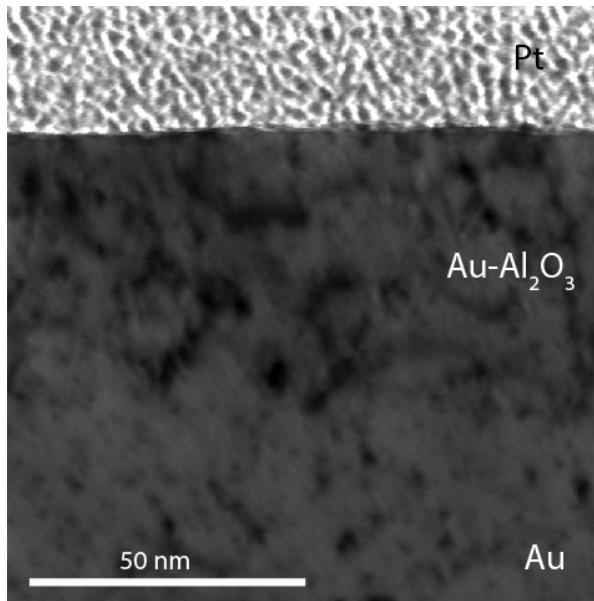
Composite Contact Material



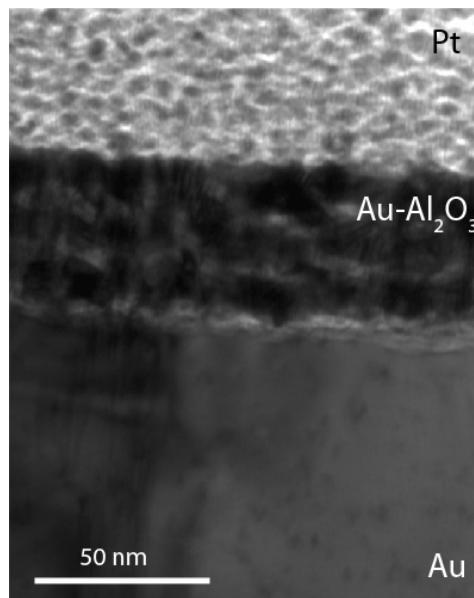
Pulsed-laser deposition (PLD) was used to create thin $\text{Au-Al}_2\text{O}_3$ electrical contact film composites of varied composition



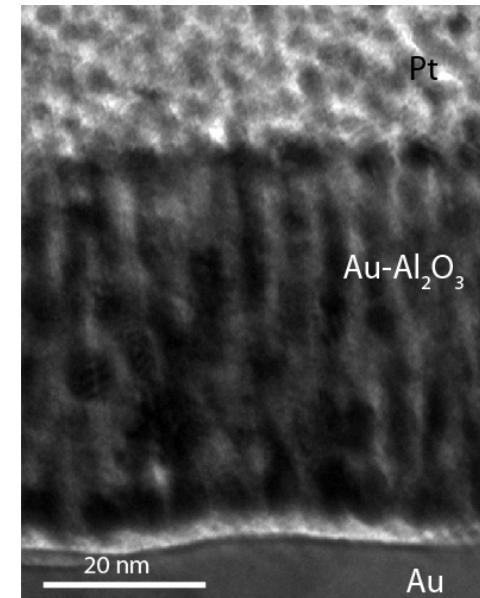
Au-Al₂O₃ TEM Imagery



90% Au



50% Au

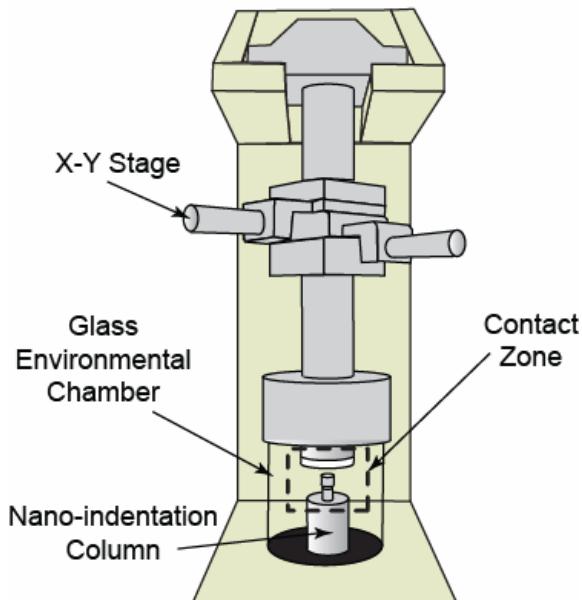


20% Au

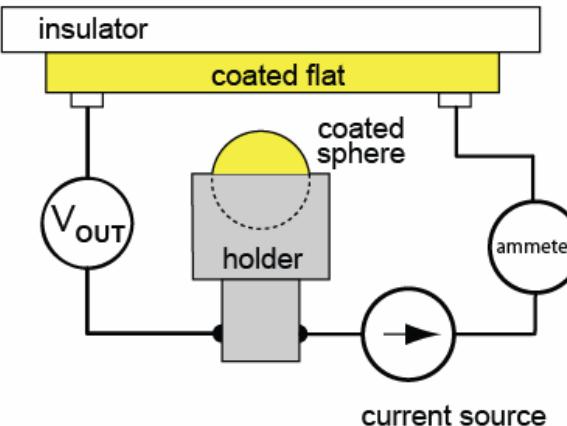
Transmission Electron Microscopy (TEM) imagery of the gold-alumina composites shows evolving morphology within the composite film as gold content decreases

Experimental Apparatus

Apparatus Schematic



Contact Zone Schematic

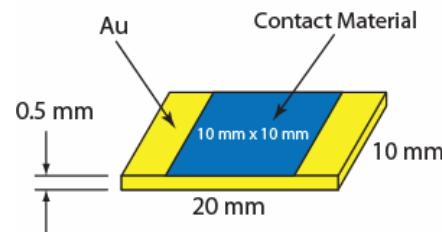


Conditions

$$F_n = 100 \mu\text{N} (\pm 1 \mu\text{N})$$

$$V_{\text{open}} = 1 \text{ V} (\pm 1 \mu\text{V} @ 1 \text{ V})$$

$$I_{\text{source}} = 1 \text{ mA} (\pm 1 \text{ nA} @ 1 \text{ mA})$$

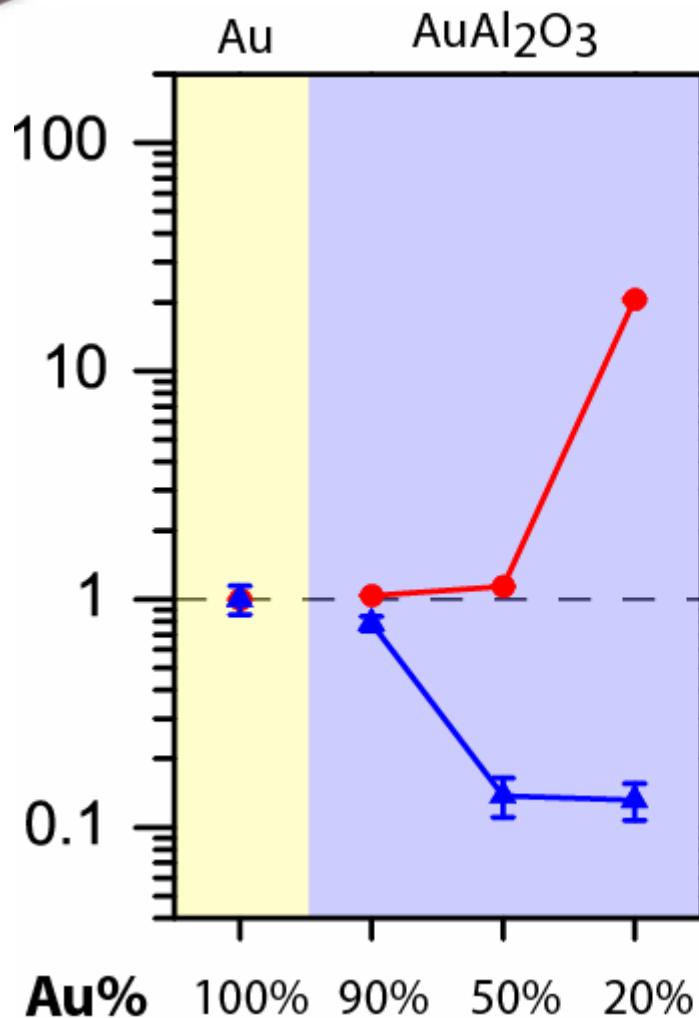


coated flat		
0	Si (substrate)	
1	Ti (adhesion layer) 100 nm	
2	Au (conductive underlayer) 500 nm	
	composite	50 nm

0.8 mm radius		
2	Au (primary contact material) 500 nm	
1	Ti (adhesion layer) 100 nm	
0	Si ₃ N ₄ (substrate)	

coated sphere

Experimental Results



- Normalized Resistance
- ▲ Normalized Pull-off Force

Normalization Values

$$R_{\text{AuAu}} = 533 \pm 7 \text{ m}\Omega$$

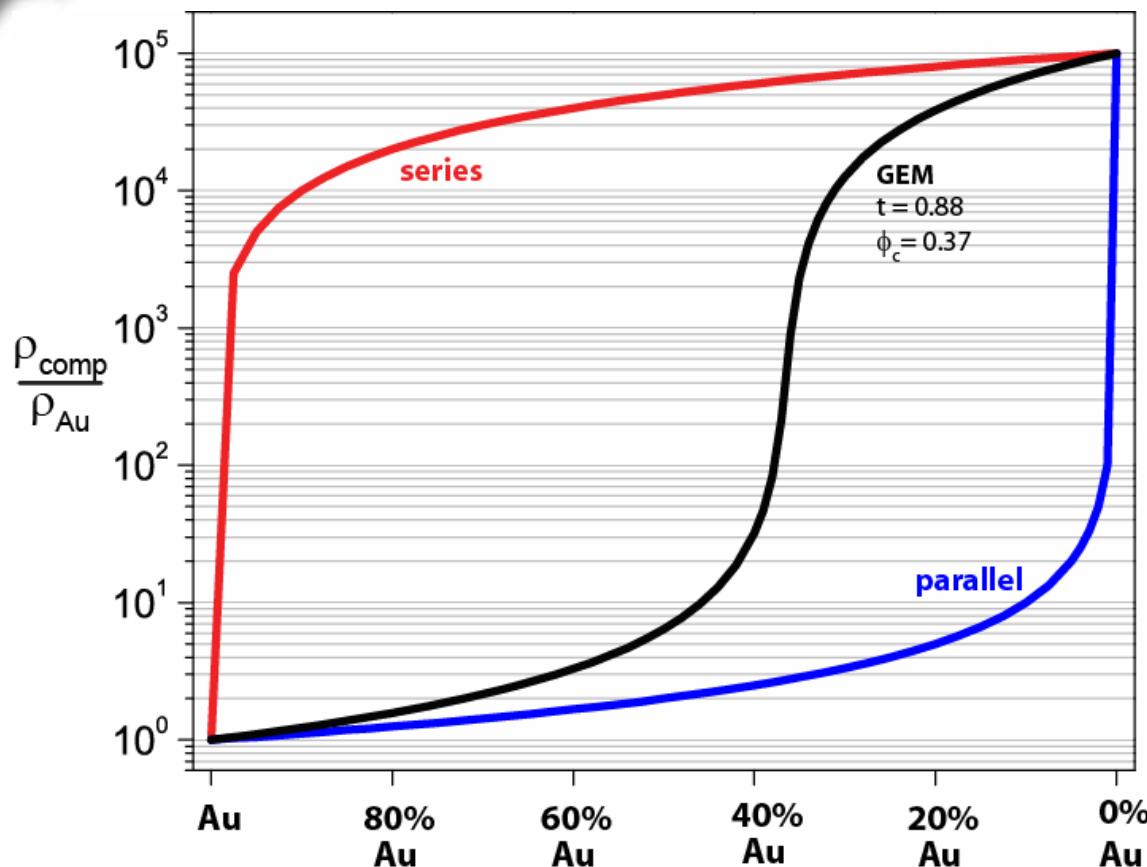
$$F_{\text{po}_{\text{AuAu}}} = 253 \pm 36 \text{ mN}$$

Experimental Conditions

Fn: 100 μN
current: 1 mA
laboratory air
22 °C
RH 20% \pm 5%

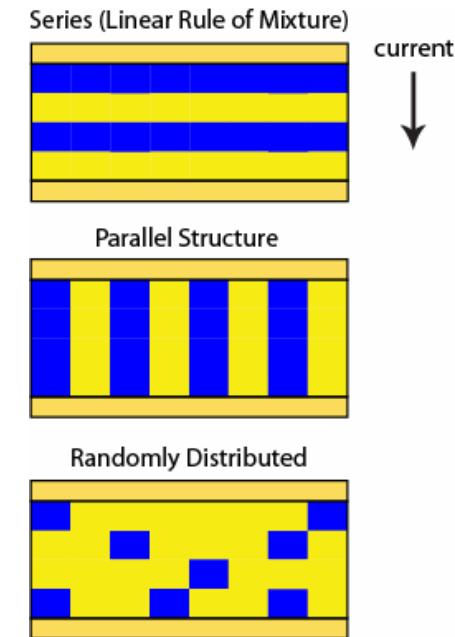
Initial experimental results showed that reduction in adhesive pull-off force did not immediately coincide with increases in measured contact resistance

Percolation Threshold



General Effective Media
(McLachlan 1987)

$$\frac{(1-\phi)\left(\rho_m^{1/t} - \rho_h^{1/t}\right)}{\rho_m^{1/t} + \rho_h^{1/t} \left(\frac{1-\phi_c}{\phi_c}\right)} + \frac{\phi\left(\rho_m^{1/t} - \rho_l^{1/t}\right)}{\rho_m^{1/t} + \rho_l^{1/t} \left(\frac{1-\phi_c}{\phi_c}\right)} = 0$$

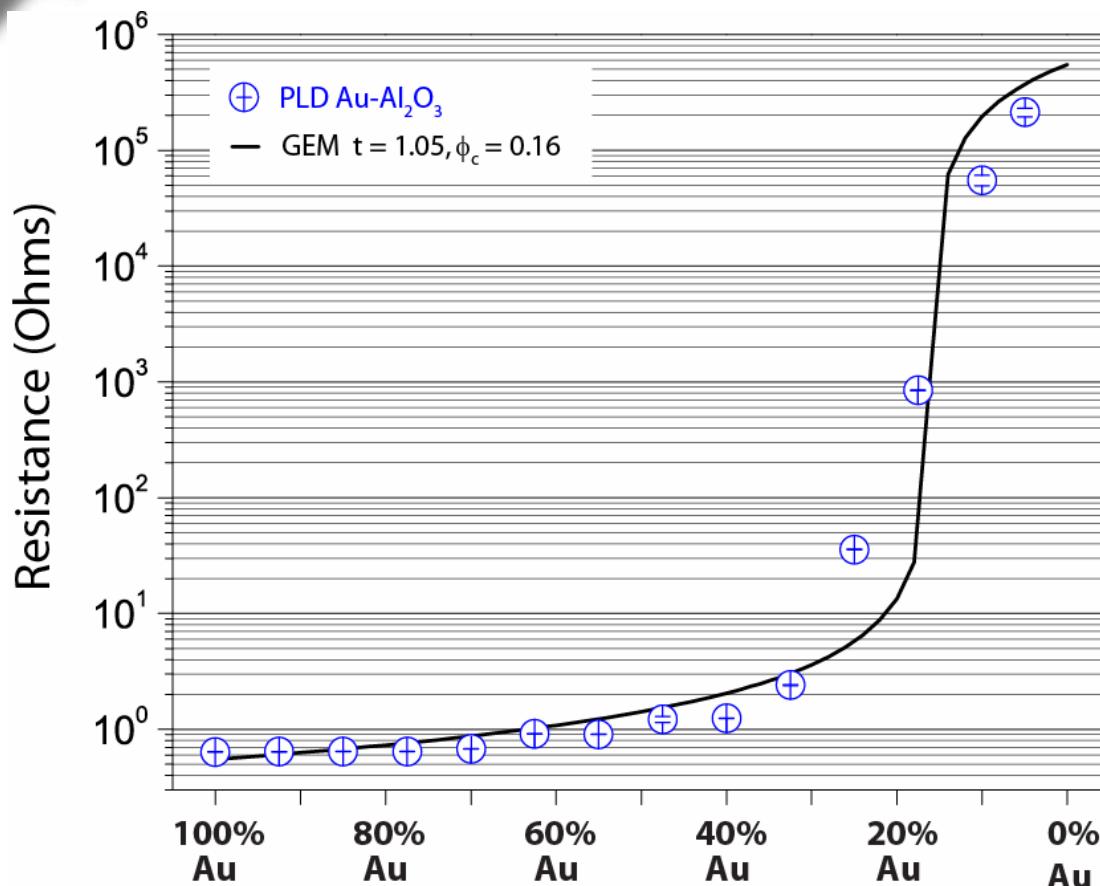


unknown parameters
 ρ_m -- composite resistivity

known parameters
 ρ_l -- low resistivity phase
 ρ_h -- high resistivity phase
 ϕ -- volume fraction

free parameters
 t -- percolation exponent
 ϕ_c -- critical volume fraction

Percolation Threshold



General Effective Media

$$\frac{(1-\phi)\left(\rho_m^{1/t} - \rho_h^{1/t}\right)}{\rho_m^{1/t} + \rho_h^{1/t} \left(\frac{1-\phi_c}{\phi_c}\right)} + \frac{\phi\left(\rho_m^{1/t} - \rho_l^{1/t}\right)}{\rho_m^{1/t} + \rho_l^{1/t} \left(\frac{1-\phi_c}{\phi_c}\right)} = 0$$

Subsequent testing of composites created with increased compositional resolution showed a distinct threshold where contact resistance increases sharply with small increase in filler percentage

unknown parameters

ρ -- composite resistivity

known parameters

ρ_L -- low resistivity phase

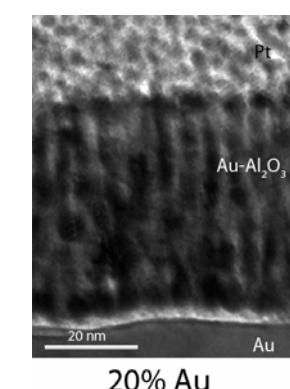
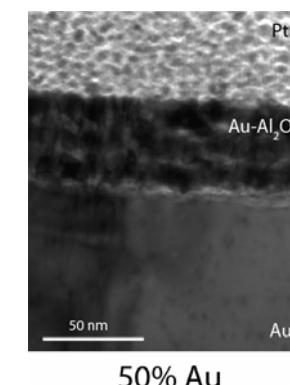
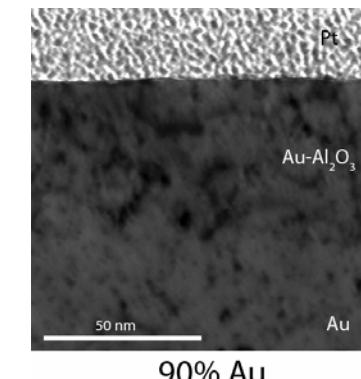
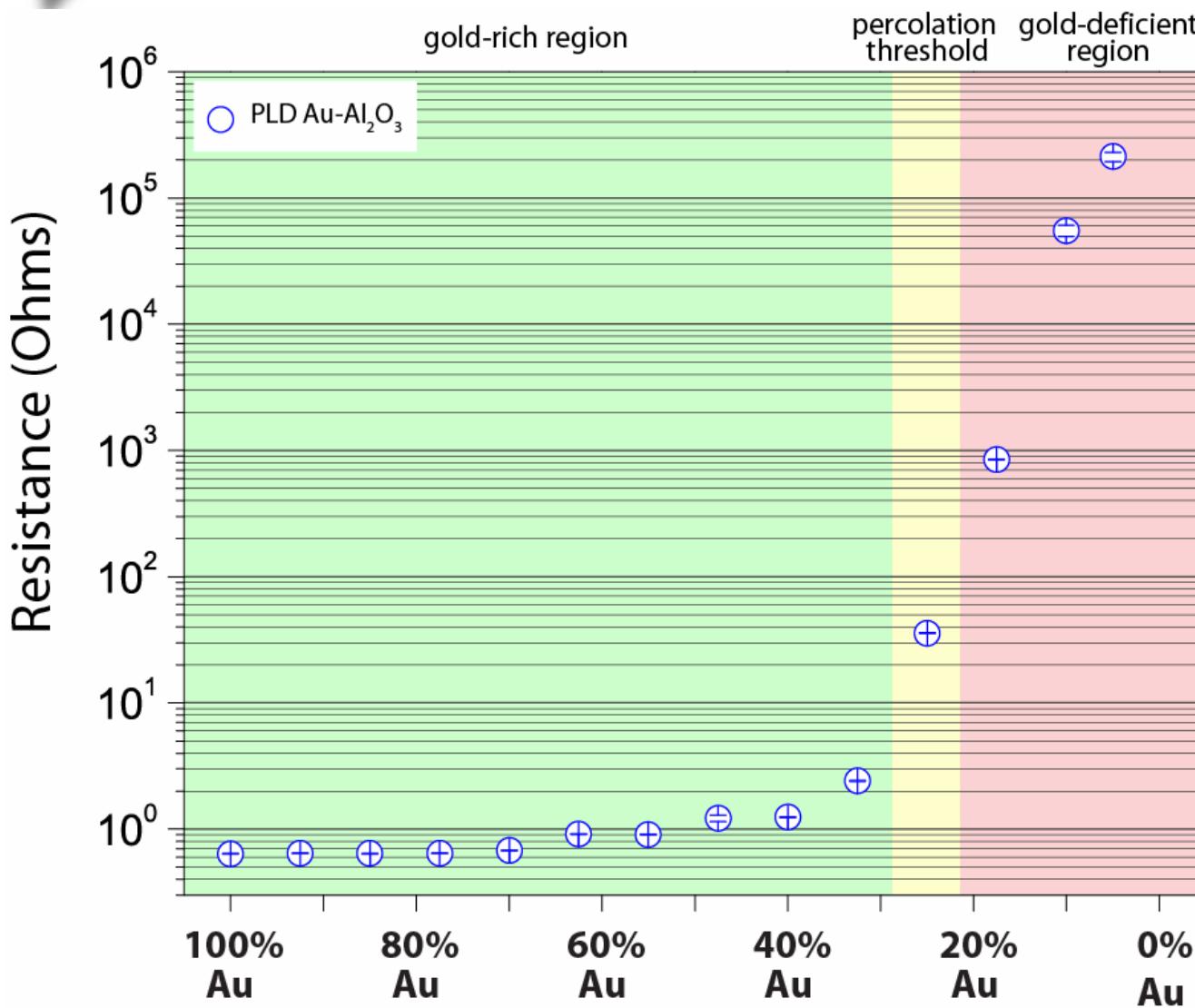
ρ_h -- high resistivity phase
 ϕ -- volume fraction

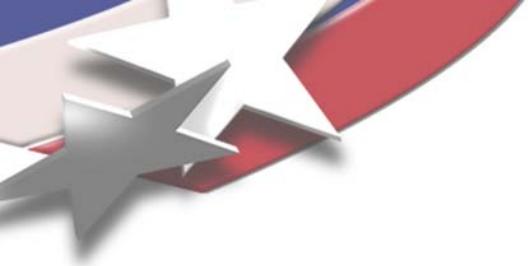
free parameters

τ – percolation exponent

ϕ_c -- critical volume fraction

Percolation Threshold





Conclusions

- Co-deposited thin film electrical contact composites can be created which simultaneously exhibit good conductivity and reduced adhesion compared to a self-mated purely metallic contact
- The nano-scale structural morphology of the composite film strongly determines the effectiveness of the composite at conducting electrical current (percolation limit)
- Significant freedom exists in the deposition methods (co-sputtering, evaporation, etc.) used to create the composite films, as well as the materials available for use
- Significant refinement and optimization of the deposited film structure could lead to highly conductive, non-adherent electrical contact materials for high-reliability MEMS devices (!)



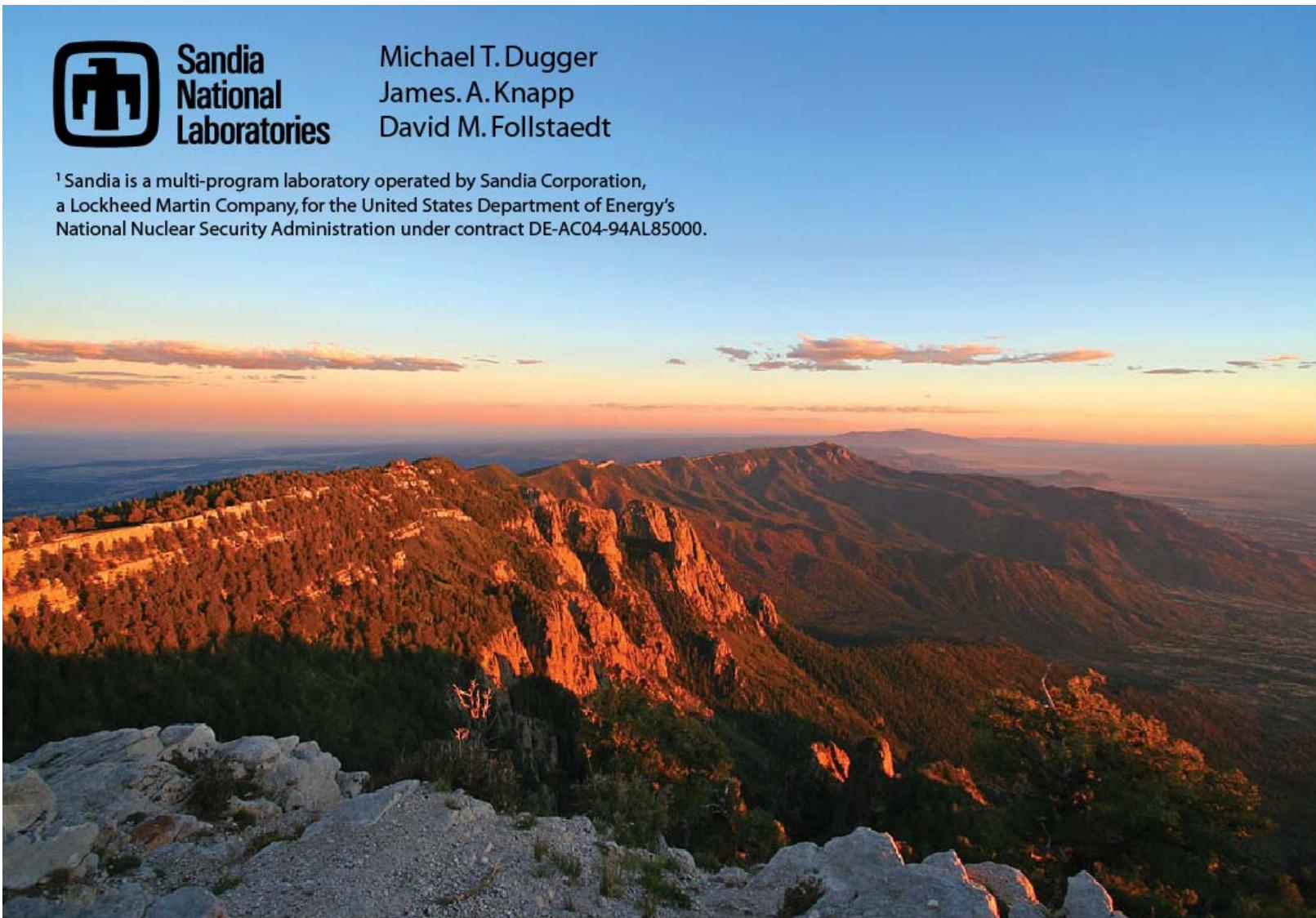
Acknowledgements and Questions



**Sandia
National
Laboratories**

Michael T. Dugger
James A. Knapp
David M. Follstaedt

¹ Sandia is a multi-program laboratory operated by Sandia Corporation, a Lockheed Martin Company, for the United States Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.



Sandia National Laboratories